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(54) Title: High-Frequency Switching Circuit

Rest Available Conv

(57) [Abstract]

[Objective] A high-frequency switching circuit is configured to operate only at a positive potential without a need for a circuit for generating a negative potential. Thereby, a small-sized device, improvement of S/N, and low power consumption are achieved while inhibiting heat generation or generation of a noise.

[Configuration] A bias voltage at a positive potential (+4V) is applied to a source electrode and a drain electrode of a switching device 1 comprising a MES type FET on a fixed basis. The positive potential (+4V) which is equipotential to the bias voltage at the above positive potential or a ground potential is selectively applied to a gate electrode as a control voltage to cause the switching device 1 to be turned ON and OFF.

